MSKSEMI 美森科













FSD

TV

TSS

MOV

GDT

PIFD

BAV316

Product specification





FEATURES

- Very Small Plastic Package
- High Switching Speed

APPLICATIONS

 High-Speed Switching in e.g. Surface Mounted Circuits

Reference News

PACKAGE OUTLINE	PIN CONFIGURATION	Marking
		XX
SOD-323		

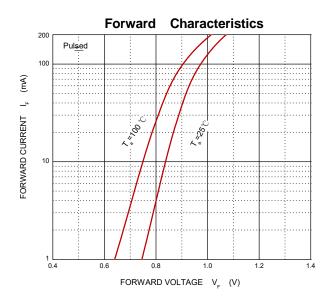
MAXIMUM RATINGS (Ta=25 $^{\circ}$ C unless otherwise noted)

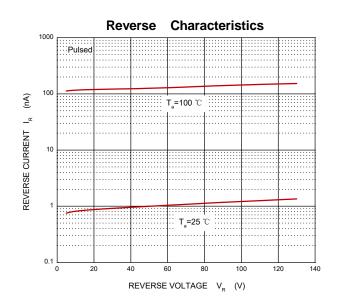
Symbol	Parameter	Value	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	130	V
V _R	DC Blocking Voltage	130	V
lo	Continuous Forward Current	215	mA
I _{FSM}	Non-repetitive Peak Forward SurgeCurrent@t= 8.3ms	2.0	Α
PD	Power Dissipation	250	mW
Reja	Thermal Resistance from Junction to Ambient	500	°C/W
T _J ,T _{stg}	Operation Junction an Storage Temperature Range	-55~+150	°C

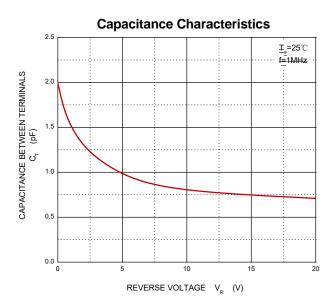
ELECTRICAL CHARACTERISTICS(Ta=25℃ unless otherwise specified)

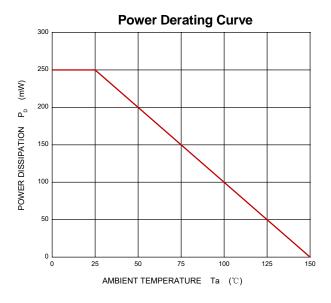
Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Reverse breakdown voltage	V (BR)	130				l _R =100µA
	V _{F1}			0.85	V	l _F =1mA
Forward voltage	V _{F2}			0.95	V	I _F =10mA
	V_{F3}			1	V	I _F =50mA
	V _{F4}			1.1	V	I _F =150mA
Reverse current	l _R			5	nA	V _R =75V
Diode capacitance	Ctot		2		pF	V _R =0V,f=1MHz
Reverse recovery time	t _{rr}			3	μs	$I_F=I_R=10$ mA, $I_{rr}=0.1\times I_R$, $R_L=100\Omega$





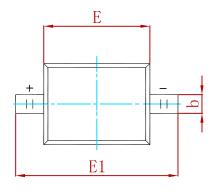


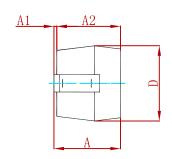


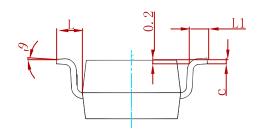




PACKAGE MECHANICAL DATA

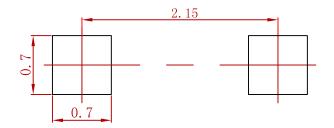






Cymphal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α		1.000		0.039	
A1	0.000	0.100	0.000	0.004	
A2	0.800	0.900	0.031	0.035	
b	0.250	0.350	0.010	0.014	
С	0.080	0.150	0.003	0.006	
D	1.200	1.400	0.047	0.055	
E	1.600	1.800	0.063	0.071	
E1	2.550	2.750	0.100	0.108	
L	0.475	REF.	0.019	REF.	
L1	0.250	0.400	0.010	0.016	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Centrolling dimension:in millimeters.
- 2.General-tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BAV316	SOD-323	3000



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